Vishay Semiconductors

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Hyperfast Rectifier, 30 A FRED Pt®



LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS						
I _{F(AV)} 30 A						
V _R	600 V					
V _F at I _F	1.40 V					
t _{rr} (typ.)	22 ns					
T _J max.	175 °C					
Package	2L TO-220 FullPAK					
Circuit configuration	Single					

FEATURES

- Hyperfast soft recovery time
- · Low forward voltage drop
- 175 °C operating junction temperature
- · Low leakage current
- Fully isolated package (V_{INS} = 2500 V_{RMS})
- True 2 pin package
- Designed and qualified according to JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

Hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of switch mode power supplies and inverters (air conditioning, high-frequency welding, UPS, and motor drives)

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

MECHANICAL DATA

Case: 2L TO-220 FullPACK

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Peak repetitive reverse voltage	V _{RRM}		600	V				
Average rectified forward current in DC	I _{F(AV)}		30	^				
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	280	A				
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +175	°C				

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL TEST CONDITIONS MIN. TYP.					UNITS	
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	600	-	-	.,	
Forward voltage	V _F	I _F = 30 A	-	1.70	2.15	V	
Torward voltage		I _F = 30 A, T _J = 150 °C	= 30 A, T _J = 150 °C - 1.40				
Reverse leakage current	I	$V_{R} = V_{R}$ rated	-	0.02	10		
Reverse leakage current	IR	$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$ - 36		36	300	μA	
Junction capacitance	CT	V _R = 600 V	-	19	-	pF	

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1

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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25 \text{ °C}$ unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS			
		$I_F = 1 \text{ A}, dI_F/dt = 100$	$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 100 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$			-			
Reverse recovery time	t _{rr}	T _J = 25 °C		-	90	-	ns A nC		
		T _J = 125 °C		-	110	-			
Deal and a second		T _J = 25 °C	l _F = 30 A, dl _F /dt = 200 A/µs,	-	4.1	-			
Peak recovery current	I _{RRM}	T _J = 125 °C	$V_{\rm B} = 400 \text{ V}$	-	9.4	-			
Reverse recovery charge	Q _{rr}	T _J = 25 °C] ``	-	230	-			
		T _J = 125 °C		-	730	-			

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C		
Thermal resistance, junction-to-case	R _{thJC}		-	2.40	3.10			
Thermal resistance, junction-to-ambient	R _{thJA}	Typical socket mount	-	45	-	°C/W		
Typical thermal resistance, case-to-heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.5	-			
Weight			-	2	-	g		
Weight			-	0.07	-	oz.		
Mounting torque			6 (5)	-	12 (10)	kgf · cm (lbf · in)		
Marking device		Case style 2L TO-220 FullPAK	ETH3106FP					



VS-ETH3106FP-N3

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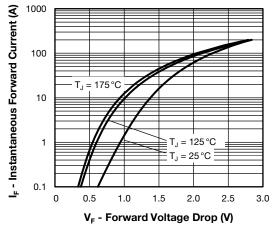


Fig. 1 - Forward Voltage Drop Characteristics

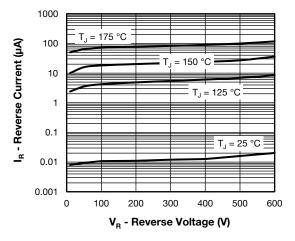


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

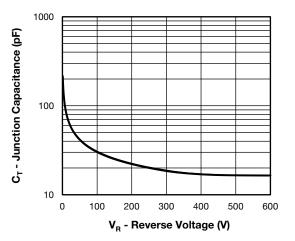


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

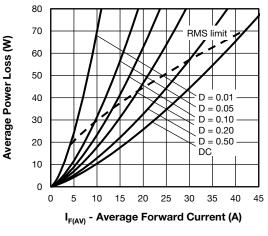
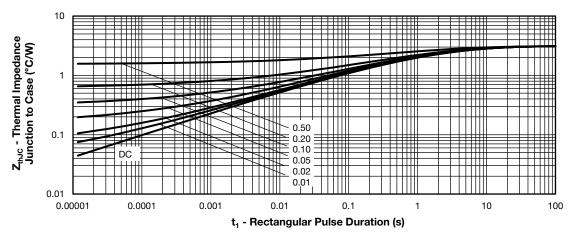


Fig. 4 - Forward Power Loss Characteristics





 Revision: 17-Dec-2020
 3
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VS-ETH3106FP-N3

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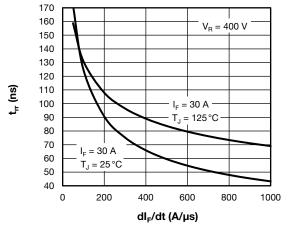


Fig. 6 - Typical Reverse Recovery Time vs. dl_F/dt

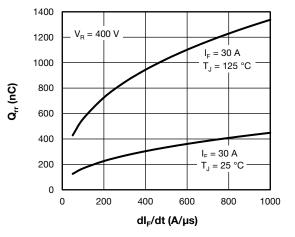


Fig. 7 - Typical Reverse Recovery Charge vs. dl_F/dt

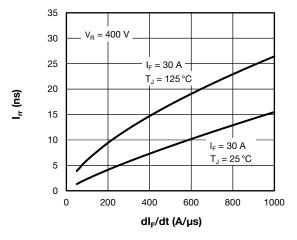


Fig. 8 - Typical Reverse Recovery Current vs. dl_F/dt



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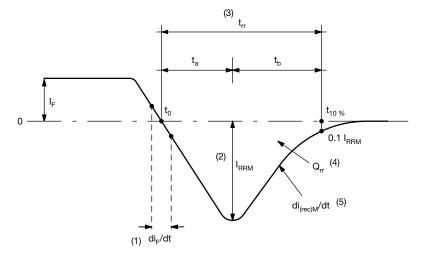


Fig. 9 - Reverse Recovery Waveform and Definitions

Notes

- $^{(1)}$ di_F/dt rate of change of current through zero crossing
- $^{(2)}$ I_{RRM} peak reverse recovery current
- $^{(3)}$ t_{rr} reverse recovery time measured from t₀, crossing point of negative going I_F, to point t_{10%}, 0.1 I_{RRM}
- $^{(4)}$ $\, \dot{Q}_{rr}$ area under curve defined by t_0 and $t_{10}\,_{\%}$

$$Q_{rr} = \int_{t_0}^{t_{10\%}} I(t) dt$$

 $^{(5)}$ di_{(rec)}M/dt - peak rate of change of current during t_b portion of t_{rr}

ORDERING INFORMATION TABLE

Device code

code	VS-	E	т	н	31	06	FP	-N3
		2	3	4	5	6	7	8
	1	- Vis	shay Sem	nicondu	ctors pr	oduct		
	2	- Ci	rcuit cont	iguratio	n:			
		E =	= single					
	3	- T:	T = TO-220					
	4	- H	H = hyperfast recovery time					
	5	- Cı	irrent coo	de: 31 =	30 A			
	6	- Vo	Itage coo	de: 06 =	600 V			
	7	- FP	FP = 2L TO-220 FullPAK					
	8	- En	vironmer	ntal digit	:			
		-N	3 = halog	gen-free	, RoHS-	-complia	ant, and	totally

LINKS TO RELATED DOCUMENTS					
Dimensions www.vishay.com/doc?96157					
Part marking information	www.vishay.com/doc?95392				

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